



## Features

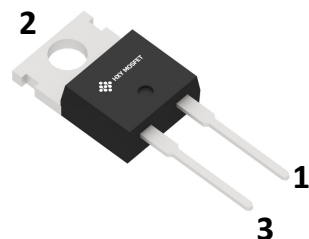
- 1.2kV Schottky Rectifier
- Zero Reverse Recovery Current
- High-Frequency Operation
- Temperature-Independent Switching
- Extremely Fast Switching
- Positive Temperature Coefficient on  $V_F$

## Benefits

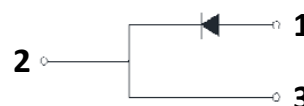
- Replace Bipolar with Unipolar Rectifiers
- Essentially No Switching Losses
- Higher Efficiency
- Reduction of Heat Sink Requirements
- Parallel Devices Without Thermal Runaway

## Applications

- Switch Mode Power Supplies (SMPS)
- Boost diodes in PFC or DC/DC stages
- Free Wheeling Diodes in Inverter stages
- AC/DC converters



TO-220C-2L



| Part Number | Package    | Marking   |
|-------------|------------|-----------|
| C4D05120A   | TO-220C-2L | C4D05120A |

## Maximum Ratings ( $T_C=25^{\circ}\text{C}$ unless otherwise specified)

| Symbol        | Parameter                             | Value          | Unit                 | Test Conditions                                                                                                         | Note   |
|---------------|---------------------------------------|----------------|----------------------|-------------------------------------------------------------------------------------------------------------------------|--------|
| $V_{RRM}$     | Repetitive Peak Reverse Voltage       | 1200           | V                    |                                                                                                                         |        |
| $V_{RSM}$     | Surge Peak Reverse Voltage            | 1300           | V                    |                                                                                                                         |        |
| $V_R$         | DC Peak Reverse Voltage               | 1200           | V                    |                                                                                                                         |        |
| $I_F$         | Continuous Forward Current            | 19<br>9.5<br>5 | A                    | $T_C=25^{\circ}\text{C}$<br>$T_C=135^{\circ}\text{C}$<br>$T_C=161^{\circ}\text{C}$                                      | Fig. 3 |
| $I_{FRM}$     | Repetitive Peak Forward Surge Current | 26<br>18       | A                    | $T_C=25^{\circ}\text{C}$ , $t_p=10$ ms, Half Sine Pulse<br>$T_C=110^{\circ}\text{C}$ , $t_p=10$ ms, Half Sine Pulse     |        |
| $I_{FSM}$     | Non-Repetitive Forward Surge Current  | 46<br>36       | A                    | $T_C=25^{\circ}\text{C}$ , $t_p=10$ ms, Half Sine Pulse<br>$T_C=110^{\circ}\text{C}$ , $t_p=10$ ms, Half Sine Pulse     | Fig. 8 |
| $I_{FMax}$    | Non-Repetitive Peak Forward Current   | 400<br>320     | A                    | $T_C=25^{\circ}\text{C}$ , $t_p=10$ $\mu\text{s}$ , Pulse<br>$T_C=110^{\circ}\text{C}$ , $t_p=10$ $\mu\text{s}$ , Pulse | Fig. 8 |
| $P_{tot}$     | Power Dissipation                     | 100<br>43      | W                    | $T_C=25^{\circ}\text{C}$<br>$T_C=110^{\circ}\text{C}$                                                                   | Fig. 4 |
| dV/dt         | Diode dV/dt ruggedness                | 200            | V/ns                 | $V_R=0-650\text{V}$                                                                                                     |        |
| $\int i^2 dt$ | $i^2t$ value                          | 10.6<br>6.5    | $\text{A}^2\text{s}$ | $T_C=25^{\circ}\text{C}$ , $t_p=10$ ms<br>$T_C=110^{\circ}\text{C}$ , $t_p=10$ ms                                       |        |
| $T_j$         | Operating Junction Range              | -55 to<br>+175 | $^{\circ}\text{C}$   |                                                                                                                         |        |
| $T_{stg}$     | Storage Temperature Range             | -55 to<br>+135 | $^{\circ}\text{C}$   |                                                                                                                         |        |
|               | TO220-2L Mounting Torque              | 1<br>8.8       | Nm<br>lbf-in         | M3 Screw<br>6-32 Screw                                                                                                  |        |



## Electrical Characteristics

| Symbol | Parameter                 | Typ.            | Max.       | Unit          | Test Conditions                                                                                                                                                                                                    | Note   |
|--------|---------------------------|-----------------|------------|---------------|--------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|--------|
| $V_F$  | Forward Voltage           | 1.4<br>1.9      | 1.8<br>3   | V             | $I_F = 5\text{ A}$ $T_J = 25^\circ\text{C}$<br>$I_F = 5\text{ A}$ $T_J = 175^\circ\text{C}$                                                                                                                        | Fig. 1 |
| $I_R$  | Reverse Current           | 20<br>40        | 150<br>300 | $\mu\text{A}$ | $V_R = 1200\text{ V}$ $T_J = 25^\circ\text{C}$<br>$V_R = 1200\text{ V}$ $T_J = 175^\circ\text{C}$                                                                                                                  | Fig. 2 |
| $Q_C$  | Total Capacitive Charge   | 27              |            | nC            | $V_R = 800\text{ V}$ , $I_F = 5\text{ A}$<br>$di/dt = 200\text{ A}/\mu\text{s}$<br>$T_J = 25^\circ\text{C}$                                                                                                        | Fig. 5 |
| C      | Total Capacitance         | 390<br>27<br>20 |            | pF            | $V_R = 0\text{ V}$ , $T_J = 25^\circ\text{C}$ , $f = 1\text{ MHz}$<br>$V_R = 400\text{ V}$ , $T_J = 25^\circ\text{C}$ , $f = 1\text{ MHz}$<br>$V_R = 800\text{ V}$ , $T_J = 25^\circ\text{C}$ , $f = 1\text{ MHz}$ | Fig. 6 |
| $E_C$  | Capacitance Stored Energy | 8.0             |            | $\mu\text{J}$ | $V_R = 800\text{ V}$                                                                                                                                                                                               | Fig. 7 |

Note: This is a majority carrier diode, so there is no reverse recovery charge.

## Thermal Characteristics

| Symbol          | Parameter                                | Typ. | Unit                      | Note   |
|-----------------|------------------------------------------|------|---------------------------|--------|
| $R_{\theta JC}$ | Thermal Resistance from Junction to Case | 1.5  | $^\circ\text{C}/\text{W}$ | Fig. 9 |

## Typical Performance

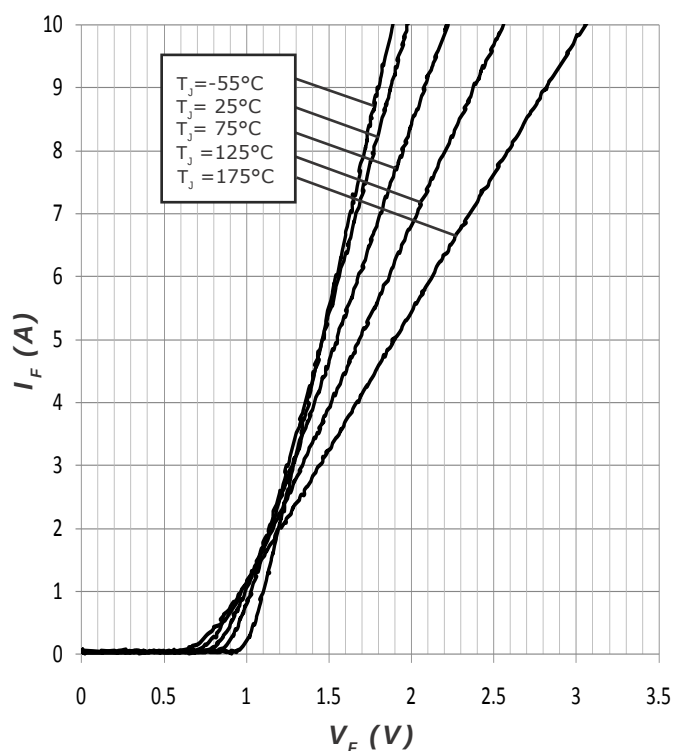


Figure 1. Forward Characteristics

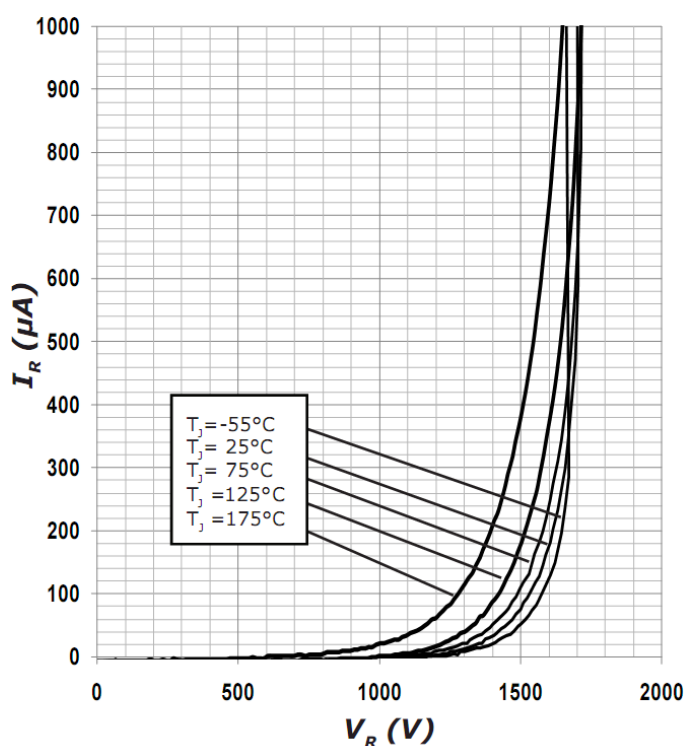


Figure 2. Reverse Characteristics



## Typical Performance

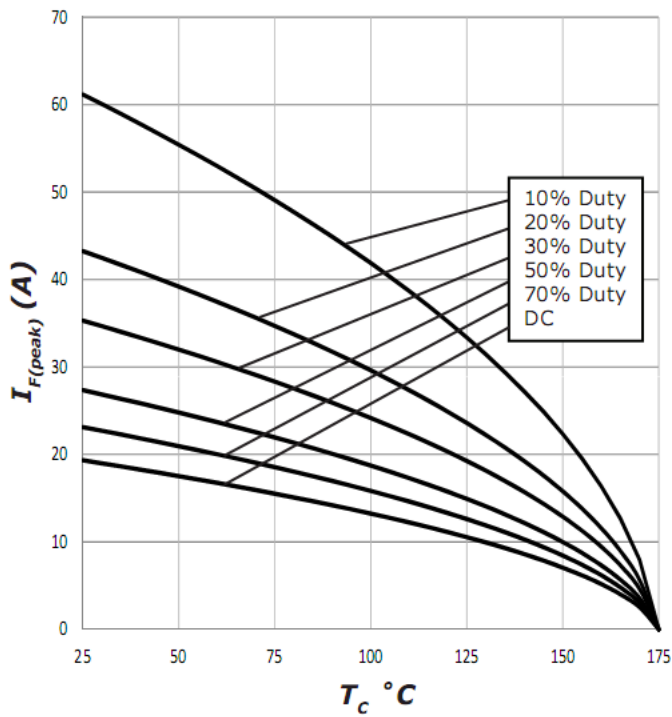


Figure 3. Current Derating

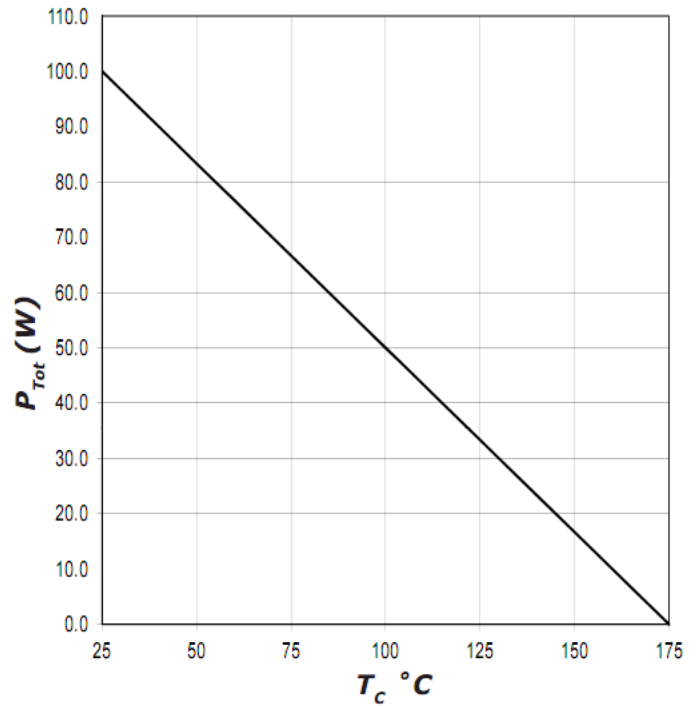


Figure 4. Power Derating

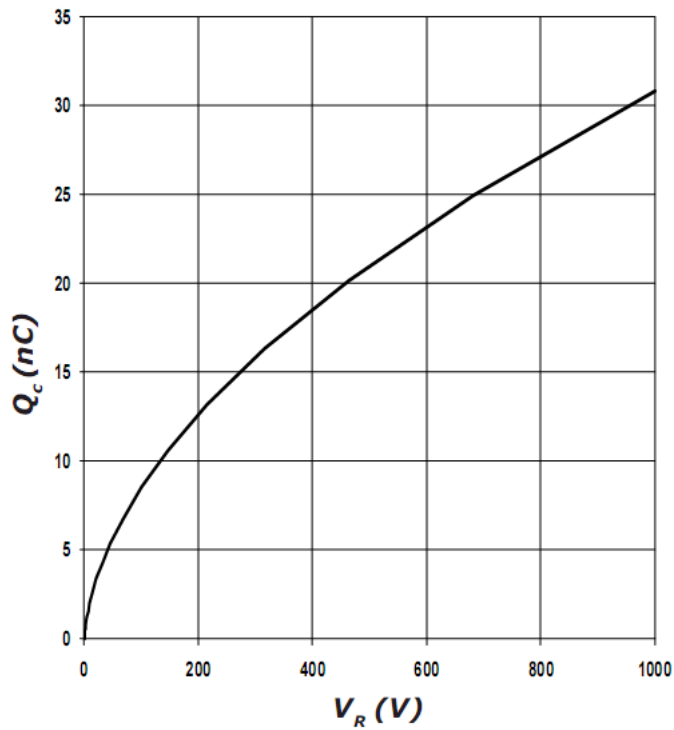


Figure 5. Recovery Charge vs. Reverse Voltage

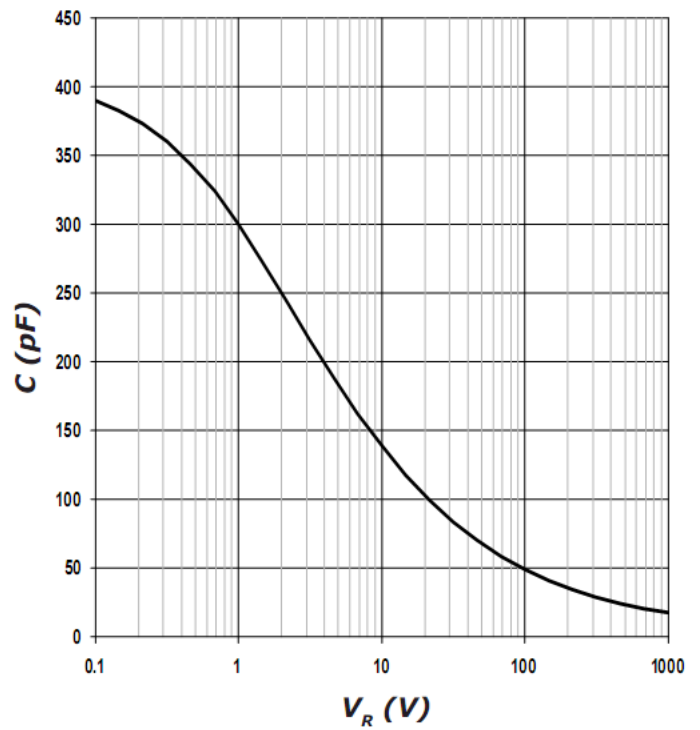
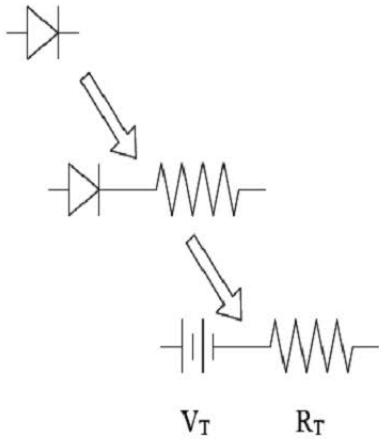


Figure 6. Capacitance vs. Reverse Voltage



## Diode Model



$$V_{f_T} = V_T + I_f * R_T$$

$$V_T = 0.96 + (T_j * -1.22 * 10^{-3})$$

$$R_T = 0.08 + (T_j * 8.5 * 10^{-4})$$

**Note:**  $T_j$  is diode junction temperature in degrees Celsius



## Package Information TO-220C-2L



| SYMBOL | DIMENSIONS |       |       | NOTES |
|--------|------------|-------|-------|-------|
|        | MIN.       | NOM.  | MAX.  |       |
| A      | 4,24       | 4,44  | 4,64  |       |
| A1     | 1.15       | 1.27  | 1.40  |       |
| A2     | 2.30       | 2,48  | 2,70  |       |
| b      | 0.70       | 0.80  | 0.90  |       |
| b1     | 1.20       | 1,55  | 1,75  |       |
| b2     | 1,20       | 1,45  | 1,70  |       |
| c      | 0.40       | 0.50  | 0.60  |       |
| D      | 14,70      | 15,37 | 16,00 | 4     |
| D1     | 8,82       | 8,92  | 9,02  |       |
| D2     | 12,43      | 12,73 | 12,83 | 5     |
| E      | 9,96       | 10,16 | 10,36 | 4,5   |
| E1     | 6,86       | 7,77  | 8,89  | 5     |
| E3*    | 8,70REF.   |       |       |       |
| e      | 2,54BSC    |       |       |       |
| e1     | 5,08BSC    |       |       |       |
| H1     | 6,30       | 6,45  | 6,60  | 5,6   |
| L      | 13,47      | 13,72 | 13,97 |       |
| L1     | 3,60       | 3,80  | 4,00  |       |
| ØP     | 3,75       | 3,84  | 3,93  |       |
| Q      | 2,60       | 2,80  | 3,00  |       |
| Q1*    | 1,73REF.   |       |       |       |
| R*     | 1,82REF.   |       |       |       |

## Recommended Solder Pad Layout



TO-220C-2L



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